Nai-Chuan Chen

List of Publications by Year
in descending order

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23	196	1040018	1058452
papers	citations	9	14
		h-index	g-index

24	24	24	256
all docs	docs citations	times ranked	citing authors

#	Article	IF	Citations
1	Significant color space blue-shift of green OLED emitter with sustaining lifetime and substantial efficiency enhancement. Applied Physics Letters, 2017, 111, .	3.3	5
2	Color-tunable mixed photoluminescence emission from Alq3 organic layer in metal-Alq3-metal surface plasmon structure. Nanoscale Research Letters, 2014, 9, 569.	5.7	7
3	Poole-Frenkel effect on electrical characterization of Al-doped ZnO films deposited on p-type GaN. Journal of Applied Physics, 2014, 115, 113705.	2.5	12
4	Photoluminescence emission from Alq3 organic layer in metalâ€“Alq3â€“metal plasmonic structure. Applied Surface Science, 2014, 303, 319-323.	6.1	4
5	Reduction of angular dip width of surface plasmon resonance sensor by coupling surface plasma waves on sensing surface and inside metalâ€“dielectricâ€“metal structure. Journal of Vacuum Science and Technology A: Vacuum, Surfaces and Films, 2013, 31, .	2.1	4
6	Properties of coupled surface plasmon-polaritons in metal-dielectric-metal structures. Journal of Applied Physics, 2012, 112, 033111.	2.5	16
7	Diffusion-controlled effects of luminescent efficiency in InGaN/GaN light-emitting diodes. , 2011, , .		0
8	Excitation of surface plasma wave at TiN/air interface in the Kretschmann geometry. Journal of Applied Physics, 2011, 109, 043104-043104-7.	2.5	35
9	Spectral shape and broadening of emission from AlGaInP light-emitting diodes. Journal of Applied Physics, 2009, 106, 074514.	2.5	20
10	Growth and characterization of InN thin film by metal-organic vapor phase epitaxy (MOVPE) on different buffers. Physica Status Solidi C: Current Topics in Solid State Physics, 2008, 5, 1594-1599.	0.8	1
11	Redshift of edge emission from AlGaInP light-emitting diodes and correlation with electron-hole recombination lifetime. Optics Express, 2008, 16, 20759.	3.4	11
12	Junction temperature measurement of light-emitting diodes by voltage-temperature relation method. , 2007, , .		3
13	Influence of strong reverse-bias on the leakage behavior of light-emitting diodes. , 2007, , .		2
14	Electrical characterization of AlN/Si(111) interface. , 2007, , .		0
15	Electron-electron interactions in Al0.15Ga0.85Nâˆ•GaN high electron mobility transistor structures grown on Si substrates. Applied Physics Letters, 2007, 90, 022107.	3.3	10
16	Capacitanceâ€“Voltage and Currentâ€“Voltage Measurements of Nitride Light-Emitting Diodes. IEEE Transactions on Electron Devices, 2007, 54, 3223-3228.	3.0	26
17	On the Surface Sulfidation of AlGaN/GaN Schottky Contacts. , 2006, , .		0
18	Crack-free AlGaN/GaN Bragg mirrors grown on Si (111) substrates by metalorganic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2006, 3, 2014-2018.	0.8	3

#	Article	IF	Citations
19	Al0.15Ga0.85Nâˆ•GaN high electron mobility transistor structures grown on p-type Si substrates. Applied Physics Letters, 2006, 89, 132107.	3.3	5
20	Influence of hydrogenation on surface morphologies, transport, and optical properties of InN epifilms. Journal of Applied Physics, 2006, 99, 126102.	2.5	10
21	High-quality GaN films grown on Si(111) by a reversed Stranskiâ€“Krastanov growth mode. Physica Status Solidi (B): Basic Research, 2004, 241, 2698-2702.	1.5	3
22	High mobility InN films grown by metal-organic vapor phase epitaxy. Physica Status Solidi C: Current Topics in Solid State Physics, 2004, 1, 2559-2563.	0.8	19
23	On the Surface Sulfidation of AlGaN/GaN Schottky Contacts. , 0, , .		0